Rad hard MOSFET nomenclature

IR | HL | YS | 7 | 9 | 7 | 0 | 3 | 4 | C | M | – | SCS | A | 00

Transistor type

H	=	Radiation hardened HEXFET
HL	=	Rad hard logic level MOSFET
HS	=	Rad hard synchronous rectifier
HSL	=	Rad hard sync. rectifier (low inductance)

Package designator

All packages have metal lids unless otherwise noted

Blank	=	TO-204AA, AE (TO-3)
C	=	Chip / die (no package)
W	=	Wafer (no package)
E	=	LCC-18
F	=	(T2) TO-205AF (TO-39, low profile)
G	=	(M1) MO-036AB (14 lead ceramic DIP)
I	=	TO-259AA
MB	=	(D4) TO-254AA tabless, low ohmic
MK	=	TO-254AA tabless, low ohmic, surface mount lead formed – at surface plane
ML	=	(D1) TO-254AA tabless, low ohmic, surface mount lead formed – below surface plane
MS	=	(T1) TO-254AA low ohmic
N	=	(U1) SMD-1
NA	=	(U2) SMD-2 (U2L) SMD-2 with leads (“A” lead option) (U2S) SMD-2 on carrier (“D” lead option)
NJ	=	(U3) SMD-0.5, metal lid
NJC	=	SMD-0.5, ceramic lid
NKC	=	SMD-0.5e, ceramic lid, high-voltage
NM	=	(U8) SMD-0.2, metal lid
NMC	=	SMD-0.2, ceramic lid
NPC	=	SMD-0.1, ceramic lid
NS	=	(U2A) SupIR-SMD™
PB	=	Power Block, isolated
Q	=	LCC-28 (quad die)
UB	=	(UB) LCC-4, metal lid, shielded - tied to 4th pin
UBC	=	LCC-4, ceramic lid, shielded
UBCN	=	LCC-3, ceramic lid, isolated
UBN	=	LCC-3, metal lid, isolated
UC	=	(UC) LCC-6
V	=	(T8) TO-258AA
Y	=	(T3) TO-257AA
YA	=	TO-257AA tabless
YB	=	(D5) TO-257AA tabless, low ohmic
YJ	=	(Dx) TO-257AA tabless, surface mount lead formed
YK	=	TO-257AA tabless, low ohmic, surface mount lead formed
YS	=	TO-257AA low ohmic

Technology

Blank	=	Gen 4
5	=	R5
5S	=	R5, S-line
6	=	R6
6S	=	R6, S-line
7	=	R7
7S	=	R7, S-line
8	=	R8
9A	=	R9
CS	=	CoolMOS Space

Channel

Blank	=	N-channel
6	=	Mixed N and P channel
9	=	P-channel

Total dose hardness

Blank	=	100 krads(Si) “R” P-channel (G4 only)
3	=	300 krads(Si) “F”
4	=	600 krads(Si)
5	=	500 krads(Si) “G”
7	=	100 krads(Si) “R”
8	=	1000 krads(Si) “H”

Voltage

0	=	60V
1	=	100V (or 130V or 150V with voltage adder)
2	=	200V (or 250V with voltage adder)
3	=	400V
4	=	500V (or 550V with voltage adder)
C	=	600V
Y	=	20V
Z	=	30V

Die size

1	=	die size 1
2	=	die size 1.7 & 2
3	=	die size 3
4	=	die size 4
5	=	die size 5
6	=	die size 6
A	=	die size 10
Z	=	smallest size

Voltage adder

0	=	full spec rating (does not apply to 60V devices)
3	=	30V, e.g. 1x3 is 130V
4	=	50V, e.g. 2x4 is 250V or, 0x4 is 60V

Package variation

Blank	=	glass eyelet (TO-257AA)
C	=	ceramic eyelet (TO-257AA)

Pinout

(applies only to TO-257AA package)

Blank			M		
Pin1	=	Gate	Pin1	=	Drain
Pin2	=	Drain	Pin2	=	Source
Pin3	=	Source	Pin3	=	Gate

Process variation

SE = Single event effect tolerant (applicable only to R4 & R5)

Screening Level

Blank	=	no screening, COTS
IR HiRel controlled drawing, die level		
CDV	=	100% visual screening
CDH	=	H level
CDK	=	K level
IR HiRel qualified lot, packaged level		
SCX	=	TX level, equivalent
SCV	=	TXV level, equivalent
SCS	=	S level, equivalent

Lead option (see notes)

A	=	Lead form down on TO-25x (if package is SMD, then lead attached)
B	=	Lead form up on TO-25x (if package is SMD, then lead attached and formed)
C	=	Lead trimmed
D	=	On DBC carrier, applies only to SMD-1 and SMD-2

Special suffix (see bottom)

Special Suffix

00	=	Gold finish – no solder dip
01	=	CSI, customer source inspection
02	=	Gold finish & CSI
03	=	DPA
04	=	DPA & gold finish
05	=	DPA & gold finish & CSI
06	=	X-Ray
07	=	X-Ray & gold finish
08	=	X-Ray & gold finish & CSI
09	=	X-Ray & CSI